

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 03-234025

(43)Date of publication of application : 18.10.1991

(51)Int.Cl. H01L 21/318
H01L 29/784

(21)Application number : 02-031042

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(22)Date of filing : 09.02.1990

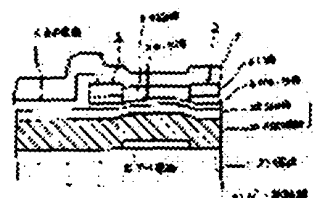
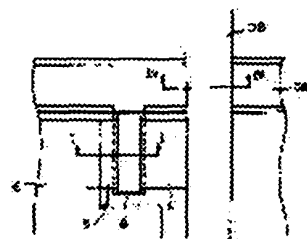
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(54) METHOD OF FORMING INSULATING THIN FILM

(57)Abstract:

PURPOSE: To form a dense insulating film of good quality having tight adhesion to the underlay and good step coverage by an atomic layer deposition process in which an object is exposed to molecular flows of different material gases several times.

CONSTITUTION: A gate electrode G of titanium film 11 is formed on a glass substrate 1. A layer is formed under a gate bus line GB, above which an aluminum film 12 is formed. A thin Al₂O₃ film 21 is formed under a gate insulating film 2 and an inner insulating film 8 by an ALE process. A silicon nitride film 22 is formed on the thin film 21 by P-CVD. An amorphous silicon layer 3, as the active semiconductor layer of a thin-film transistor, is continuously formed by P-CVD, and then there are formed an n+ amorphous silicon layer 4 as a contact layer, and a channel protecting film 6 of SiO₂. Titanium film 5 is formed to make a source electrode S, a drain electrode D, and a drain bus line DB. A display electrode E of ITO film is formed, and finally the substrate is entirely covered with surface protecting film 7 of Al₂O₃ by an ALE process.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]